



74AUP1G125

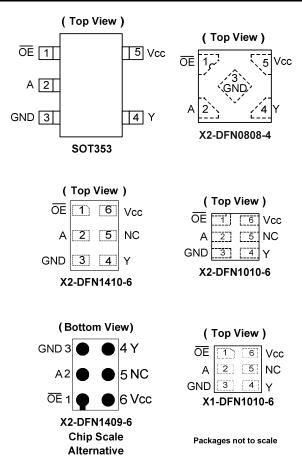
SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Description

The Advanced, Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The 74AUP1G125 is a single, non-inverting buffer/bus driver, designed for operation over a power supply range of 0.8V to 3.6V. The device has a three-state output that enters a high-impedance state when a high level is applied to the output enable (OE) pin. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing damaging current backflow when the device is powered down.

Pin Assignments



Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static Power Consumption
- I_{CC} < 0.9μA
 - Low Dynamic Power Consumption $C_{PD} = 6.3 pF$ (Typical at 3.6V)
- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250mV at V_{CC} = 3.0V.
- IOFF Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22
 2000-V Human Body Model (A114)
 - Exceeds 1000-V Charged Device Model (C101)
 - Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages Named per JESD30E
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Applications

Suited for Battery and Low Power Needs

Cell Phones, Personal Navigation / GPS

MP3 Players, Cameras, Video Recorders

Computer Peripherals, Hard Drives, SSDs, CD/DVD ROMs

PCs, Ultrabooks, Notebooks, Netbooks

TVs, DVDs, DVRs, Set-Top Boxes

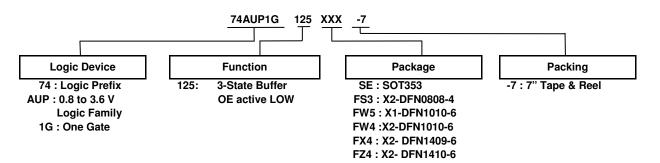
Wide array of products such as:

Tablets, E-readers

Notes:



Ordering Information



Device	Package	Package	Package	7" Tape	and Reel
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix
74AUP1G125SE-7	SE	SOT353	2.0mm x 2.0mm x 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7
74AUP1G125FS3-7	FS3	X2-DFN0808-4	0.8mm x 0.8mm x 0.35mm 0.5 mm pad pitch (diamond)	5,000/Tape & Reel	-7
74AUP1G125FW5-7	FW5	X1-DFN1010-6	1.0mm x 1.0mm x 0.5mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G125FW4-7	FW4	X2-DFN1010-6	1.0mm x 1.0mm x 0.4mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G125FX4-7	FX4	X2-DFN1409-6 Chip Scale Alternative	1.4mm x 0.9mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G125FZ4-7	FZ4	X2-DFN1410-6	1.4mm x 1.0mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7

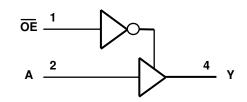
Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

Pin Descriptions

Pin Name	Function			
ŌĒ	Output Enable			
A	Data Input			
GND	Ground			
Y	Data Output			
V _{CC}	Supply Voltage			

Logic Diagram



Function Table

Inp	Inputs					
OE	Α	Y				
L	Н	Н				
L	L	L				
Н	Х	Z				



Absolute Maximum Ratings (Notes 6 & 7) (@T_A = +25 °C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
l _{IK}	Input Clamp Current VI < 0	50	mA
Ι _{ΟΚ}	Output Clamp Current ($V_O < 0$)	50	mA
lo	Continuous Output Current (V _O = 0 to V _{CC})	±20	mA
Icc	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes: 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current, or conversely, forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 8) (@T_A = +25 °C, unless otherwise specified.)

Symbol	P	arameter	Min	Max	Unit
V _{CC}	Operating Voltage		0.8	3.6	V
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	V _{CC}	V
		$V_{CC} = 0.8V$	—	-20	μA
		$V_{CC} = 1.1 V$	—	-1.1	
	Lligh Lovel Output Current	$V_{CC} = 1.4V$	—	-1.7	
I _{OH}	High-Level Output Current	V _{CC} = 1.65V	—	-1.9	mA
		V _{CC} = 2.3V	—	-3.1	
		V _{CC} = 3.0V	—	-4	
		$V_{CC} = 0.8V$	—	20	μA
		V _{CC} = 1.1V	—	1.1	
		$V_{CC} = 1.4V$	—	1.7	
IOL	Low-Level Output Current	V _{CC} = 1.65V	—	1.9	mA
		V _{CC} = 2.3V	—	3.1	
		V _{CC} = 3.0V	—	4	1
$\Delta t / \Delta V$	Input Transition Rise or Fall Rate	V _{CC} = 0.8V to 3.6V	—	200	ns/V
T _A	Operating Free-Air Temperature		-40	+125	°C

Note: 8. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

Cumhal	Deservators	Test Conditions	V	T _A = -	+25℃	T _A = -40 ℃	C to +85℃	l Init
Symbol	Parameter	Test Conditions	Vcc	Min	Max	Min	Max	Unit
		—	0.8V to 1.65V	0.80 x V _{CC}	—	0.80 x V _{CC}	_	
V	High-Level Input	_	1.65V to 1.95V	0.65 x V _{CC}	_	0.65 x V _{CC}	_	v
V _{IH}	Voltage	_	2.3V to 2.7V	1.6	_	1.6	_	v
		—	3.0V to 3.6V	2.0	—	2.0		
		—	0.8V to 1.65V	—	$0.30 \times V_{CC}$	_	$0.30 \times V_{CC}$	
VIL	Low-Level Input	—	1.65V to 1.95V	—	$0.35 \times V_{CC}$	_	$0.35 \times V_{CC}$	v
۷IL	Voltage	—	2.3V to 2.7V	—	0.7		0.7	v
		_	3.0V to 3.6V		0.9	_	0.9	
		$I_{OH} = -20\mu A$	0.8V to 3.6V	$V_{CC} - 0.1$	—	$V_{CC} - 0.1$	_	
		I _{OH} = -1.1mA	1.1V	$0.75 \times V_{CC}$	—	$0.7 \times V_{CC}$	_	
		I _{OH} = -1.7mA	1.4V	1.11	—	1.03	_	
	High-Level	I _{OH} = -1.9mA	1.65V	1.32	—	1.3		
VOH	Output Voltage	I _{OH} = -2.3mA		2.05	—	1.97		V
		I _{OH} = -3.1mA	2.3V	1.9	_	1.85	_	
		I _{OH} = -2.7mA		2.72		2.67		
	$I_{OH} = -4mA$		3V	2.6		2.55		
		$I_{OL} = 20\mu A$	0.8V to 3.6V		0.1		0.1	
		$I_{OL} = 1.1 \text{mA}$	1.1V		0.3 x V _{CC}		0.3 x V _{CC}	
		$I_{OL} = 1.7 \text{mA}$	1.4V		0.31		0.37	
	Low-Level	$I_{OL} = 1.9 \text{mA}$	1.65V	_	0.31	_	0.35	
V _{OL}	Output Voltage	$I_{OL} = 2.3$ mA	1.00 V	_	0.31		0.33	V
		$I_{OL} = 3.1 \text{ mA}$	2.3V		0.44	_	0.45	
					0.44		0.43	
		$I_{OL} = 2.7 \text{ mA}$	3V		0.44		0.35	
		I _{OL} = 4 mA A or B Input			0.44		0.45	
lı	Input Current	$V_1 = GND$ to 3.6V	0 to 3.6V	_	±0.1		±0.5	μA
IOFF	Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0	—	±0.2		±0.5	μA
loz	Z State Leakage Current	$V_{O} = 3.6V$ $V_{i} = 3.6V$	3.6V	—	±0.2	_	±0.5	μA
Δl _{OFF}	Delta Power Down Leakage Current	V_{I} or $V_{O} = 0V$ to 3.6V	0 to 0.2V	—	0.2	_	0.6	μA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	0.5	_	0.9	μA
		Data input at V_{CC} -0.6V OE= GND I _O = 0 A	3.3V	—	40	_	50	μΑ
ΔI _{CC}	Additional Supply Current	OE input at V_{CC} -0.6V Data Input = GND or Vcc, I _O = 0 A	3.3V	—	110		120	μA
		OE input at V_{CC} Data Input = GND to 3.6V $I_{O} = 0A$	0.8V to 3.6V		1		1	μΑ



Electrical Characteristics (continued) (@T_A = +25 °C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	Vcc	T _A = -40	to 125 °C	Unit	
Symbol	Parameter	Test Conditions	VCC	Min	Max	Unit	
		—	0.8V to 1.65V	0.80 x V _{CC}	—		
VIH	High-Level Input	—	1.65V to 1.95V	0.70 x V _{CC}	—	v	
VIH	Voltage	—	2.3V to 2.7V	1.6	—	v	
		_	3.0V to 3.6V	2.0	—		
		_	0.8V to 1.65V	_	0.25 x V _{CC}		
VIL	Low-Level Input	_	1.65V to 1.95V	_	$0.35 \times V_{CC}$	v	
۷IL	Voltage	—	2.3V to 2.7V	_	0.7		
		_	3.0V to 3.6V		0.9		
		I _{OH} = -20μA	0.8V to 3.6V	V _{CC} -0.11	—		
		I _{OH} = -1.1mA	1.1V	$0.6 \times V_{CC}$	—		
		I _{OH} = -1.7mA	1.4V	0.93	—		
	High-Level Output	I _{OH} = -1.9mA	1.65V	1.17	—		
V _{OH}	Voltage	I _{OH} = -2.3mA	0.01/	1.77	—	- V	
		I _{OH} = -3.1mA	2.3V	1.67	_		
		I _{OH} = -2.7mA	01/	2.40	_		
		I _{OH} = -4mA	3V	2.30	—		
		I _{OL} = 20μΑ	0.8V to 3.6V	_	0.11		
		$I_{OL} = 1.1 \text{mA}$	1.1V	_	0.3 x V _{CC}		
		$I_{OL} = 1.7 \text{mA}$	1.4V	_	0.41		
	Low-Level Output	$I_{OL} = 1.9 \text{mA}$	1.65V	_	0.39	1	
V _{OL}	Voltage	$I_{OL} = 2.3 \text{mA}$		_	0.36	- V	
	-	$I_{OL} = 3.1 \text{mA}$	2.3V	_	0.50	_	
		$I_{OL} = 2.7 \text{mA}$		_	0.36		
		$I_{OL} = 4mA$	3V -	_	0.50	-	
lı	Input Current	A or B Input VI =GND to 3.6V	0 to 3.6V	_	±0.75	μA	
IOFF	Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0	_	±3.5	μA	
	Z State	V _O = 3.6V					
loz	Leakage Current	$V_0 = 0.0V$ $V_1 = 3.6V$	3.6V		±1.5	μA	
ΔI_{OFF}	Delta Power Down Leakage Current	V _O = 3.6V V _I	0V to 0.2V	—	±2.5		
lcc	Supply Current	$V_{I} = GND \text{ or } V_{CC}, I_{O} = 0$	0.8V to 3.6V	_	3.0	μA	
-		Data Input at V_{CC} - 0.6V OE = GND I _O = 0A	3.3V	_	75	μA	
ΔI _{CC}	Additional Supply Current	OE Input at V_{CC} - 0.6V Data Input = GND or V_{CC} $I_0 = 0A$	3.3V	_	180	μA	
		OE Input at V_{CC} Data Input = GND to 3.6V $I_{O} = 0A$	0.8V to 3.6V	_	1	μA	



Switching Characteristics

Deverseter	From	То	V	•	T _A = +25℃	0	T _A = -40 °C	to+85℃	T _A = -40 ℃	to +125℃	Unit
Parameter	Input	Output	Vcc	Min	Тур	Max	Min	Max	Min	Max	
			0.8V	_	20.6	—	_	-	—	_	
			1.2V ± 0.1V	2.8	5.5	10.5	2.5	11.7	2.5	12.9	1
	А	Y	1.5V ± 0.1V	2.0	3.9	6.1	1.9	7.3	1.9	8.1	1
t _{pd}	A	ř	1.8V ± 0.15V	1.9	3.2	4.8	1.7	6.1	1.7	6.7	ns
			2.5V ± 0.2V	1.6	2.6	3.6	1.4	4.3	1.4	4.9	1
				3.3V ± 0.3V	1.2	2.4	3.1	1.2	3.9	1.2	4.4
			0.8V	_	69.9	_	—	_	—	_	- ns
			1.2V ± 0.1V	3.1	6.1	11.8	2.9	13.9	2.9	15.4	
		Y	1.5V ± 0.1V	2.3	4.2	6.6	2.2	7.7	2.2	8.3	
t _{en}	OE		1.8V ± 0.15V	2.0	3.4	5.1	1.9	6.2	1.9	6.8	
			2.5V ± 0.2V	1.8	2.6	3.7	1.7	4.5	1.7	5.0	
			3.3V ± 0.3V	1.7	2.4	3.1	1.7	3.5	1.7	3.9	
			0.8V	_	14.3	_	_	_	_	_	
			1.2V ± 0.1V	2.7	4.3	6.5	2.7	7.3	2.7	8.2	
		Y	1.5V ± 0.1V	2.1	3.2	5.1	2.1	5.7	2.1	5.7	
t _{dis} OE	OE	OE Y	1.8V ± 0.15V	2.0	3.0	4.9	2.0	5.4	2.0	5.7	- ns
			2.5V ± 0.2V	1.4	2.7	3.9	1.4	4.0	1.4	4.1	
			3.3V ± 0.3V	1.3	2.5	3.2	1.3	3.4	1.3	3.9	

C_L = 10pF, See Figure 1

Devementer	From	То	N		Γ _A = +25 °	C	T _A = -40°C	C to +85℃	T _A = -40 ℃	to +125℃	Unit
Parameter	Input	Output	Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	-	24.0		_	_	_	_	
			1.2V ± 0.1V	3.2	6.4	12.3	3.0	13.8	3.0	15.2	
	t _{pd} A	Y	1.5V ± 0.1V	2.1	4.5	7.3	1.9	8.5	1.9	9.4	
τ _{pd}		Ŷ	1.8V ± 0.15V	1.9	3.8	5.5	1.7	6.8	1.7	7.6	ns
			2.5V ± 0.2V	1.7	3.2	4.2	1.6	5.3	1.6	5.9	
			3.3V ± 0.3V	1.4	3.0	3.8	1.4	4.6	1.4	5.2	
			0.8V	_	73.7		_	_	—		- ns
			1.2V ± 0.1V	3.6	6.9	13.5	3.4	15.8	3.4	17.5	
		Y	1.5V ± 0.1V	2.3	4.8	7.7	2.2	8.6	2.2	9.4	
t _{en}	ŌĒ		1.8V ± 0.15V	2.0	3.9	5.8	1.9	6.8	1.9	7.4	
			2.5V ± 0.2V	1.8	3.2	4.3	1.7	5.3	1.7	5.9	
			3.3V ± 0.3V	1.7	3.0	3.9	1.7	4.3	1.7	4.8	
			0.8V	_	32.7	—	_	_	—	_	
			1.2V ± 0.1V	3.4	5.4	7.9	3.4	8.8	3.4	9.9	
		ΞY	1.5V ± 0.1V	2.2	4.1	5.5	2.2	6.2	2.2	7.1	
t _{dis}	ŌĒ		1.8V ± 0.15V	2.2	4.2	5.6	1.9	6.3	1.9	7.1	ns
			2.5V ± 0.2V	1.7	3.0	5.2	1.7	5.5	1.7	6.1	
			3.3V ± 0.3V	1.9	3.8	4.8	1.7	5.0	1.7	5.6	



Switching Characteristics (continued)

Parameter	From	То	V _{cc}	1	Γ _A = +25 °C	C	T _A = -40 °C	Cto+85℃	T _A = -40 °C	to +125℃	Unit
Parameter	Input	Output	v cc	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	27.4	—	—	—	—	_	
			1.2V ± 0.1V	3.6	7.2	14.1	3.3	15.8	3.3	17.5	
	А	Y	1.5V ± 0.1V	3.0	5.1	8.1	2.5	9.8	2.5	10.9	
t _{pd}		ř	1.8V ± 0.15V	2.2	4.3	6.3	2.0	7.9	2.0	8.8	ns
		2.5V ± 0.2V	2.0	3.7	4.9	1.8	6.0	1.8	6.7		
		3.3V ± 0.3V	1.5	3.5	4.4	1.5	5.4	1.5	6.1		
		DE Y	0.8V	-	77.5	—	_	_	_	_	ns
			1.2V ± 0.1V	4.0	7.7	15.2	3.7	17.6	3.7	19.6	
			1.5V ± 0.1V	3.0	5.3	8.4	2.5	9.8	2.5	10.7	
t _{en}	OE		1.8V ± 0.15V	2.3	4.4	6.5	2.1	7.7	2.1	8.5	
			2.5V ± 0.2V	2.1	3.6	5.0	2.0	6.1	2.0	6.8	
			3.3V ± 0.3V	2.0	3.5	4.5	1.9	4.9	1.9	5.5	
			0.8V	_	60.8	—	_	_	_	_	
			1.2V ± 0.1V	3.8	6.5	12.3	3.7	13.3	3.7	13.3	
		E Y	1.5V ± 0.1V	2.8	5.8	10.1	2.5	10.5	2.5	10.5	
t _{dis}	OE		1.8V ± 0.15V	2.2	5.3	9.0	2.1	9.4	2.1	9.9	- ns
			2.5V ± 0.2V	2.1	5.1	7.9	2.0	8.1	2.0	8.4	
			3.3V ± 0.3V	1.9	5.0	7.0	1.9	7.5	1.9	7.5	1

CL=30pF, See Figure 1

Parameter	From	То	V		Γ _A = +25 °	C	T _A = -40 °C	C to +85℃	T _A = -40 ℃	to +125℃	Unit
Parameter	Input	Output	Vcc	Min	Тур	Max	Min	Max	Min	Max	onn
			0.8V	_	37.4		_	_	_	_	
			1.2V ± 0.1V	4.8	9.5	19.0	4.4	21.6	4.4	24.0	
	t _{pd} A	Y	1.5V ± 0.1V	4.0	6.7	10.8	3.0	13.0	3.0	14.5	
lpd		ř	1.8V ± 0.15V	2.4	5.6	8.4	2.4	10.3	2.4	11.5	ns
			2.5V ± 0.2V	2.1	4.8	6.3	2.1	7.8	2.1	8.7	
			3.3V ± 0.3V	2.0	4.6	5.8	2.0	7.5	2.0	8.3	
		0.8V	_	88.9	_	_	_	_	_		
		Y	1.2V ± 0.1V	5.2	9.9	19.8	4.8	22.8	4.8	25.3	
	OE		1.5V ± 0.1V	4.0	6.8	10.8	3.1	12.6	3.1	14.1	– ns
t _{en}	ÛE		1.8V ± 0.15V	3.0	5.6	8.5	2.8	10.2	2.8	11.3	
			2.5V ± 0.2V	2.2	4.8	6.5	2.2	8.1	2.2	8.8	
			3.3V ± 0.3V	2.1	4.6	6.0	2.1	7.5	2.1	7.7	
			0.8V	_	49.9	_	—	_	—	—	
			1.2V ± 0.1V	6.0	9.9	13.3	4.8	16.5	4.8	16.5	
		Y	1.5V ± 0.1V	2.8	9.0	12.0	3.1	13.2	3.1	14.2	
t _{dis} OE	UE	Ŷ	1.8V ± 0.15V	2.6	8.8	11.1	2.8	12.4	2.8	13.8	ns
			2.5V ± 0.2V	2.6	8.7	10.9	2.6	11.6	2.6	13.5	
			3.3V ± 0.3V	2.5	8.6	10.5	2.5	10.8	2.5	13.1	



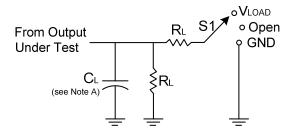
Operating and Package	Characteristics	(@T _A = +25 °C, unless otherwise specified.)
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	Parameter	Test Conditio		Vcc	Тур	Unit
		f = 1MHz		0.8V	6.9	
				1.2V ± 0.1V	6.7	
~	Power Dissipation			1.5V ± 0.1V	6.6	~_
C _{pd}	Capacitance	No Loa	d	1.8V ± 0.15V	6.5	pF
				2.5V ± 0.2V	6.4	
				3.3V ± 0.3V	6.3	1
Ci	Input Capacitance	Vi = V _{CC} or	GND	0V or 3.3V	1.5	pF
	Thermal Resistance Junction-to-Ambient	SOT353	(Note 9)	_	371	- °C/W
		X2-DFN0808-4		_	430	
		X1-DFN1010-6		_	435	
θ _{JA}		X2-DFN1010-6		_	445	
		X2-DFN1409-6		_	470	
		X2-DFN1410-6	_	460		
		SOT353		_	143	
	X	X2-DFN0808-4		_	240	
	Thermal Resistance	X1-DFN1010-6		_	250	°C/W
θJC	Junction-to-Case	X2-DFN1010-6	(Note 9)	_	250	
		X2-DFN1409-6		_	275	
		X2-DFN1410-6	1	_	265	1

Note: 9. Test condition for each of the six package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

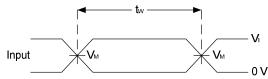


Parameter Measurement Information

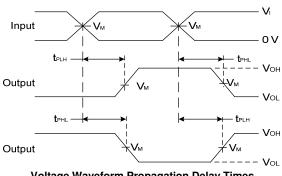


TEST	S1	RL
tplh/tphl	Open	1MΩ
t _{PLZ} /t _{PZL}	Vload	5kΩ
tphz/tpzh	GND	5kΩ

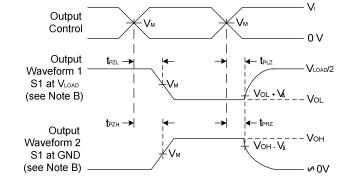
N _e .	Inputs		V V	C.	VA	
Vcc	VI	t _r /t _f	VM	VLOAD	CL	VΔ
0.8V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1V
1.2V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1V
1.5V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1V
1.8V ± 0.15V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.15V
2.5V ± 0.2V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.15V
3.3V ± 0.3V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.3V



Voltage Waveform Pulse Duration







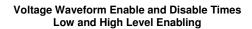


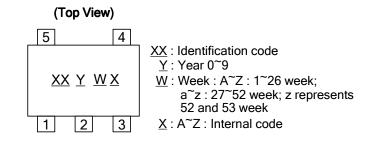
Figure 1 Load Circuit and Voltage Waveforms

- Notes: A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate \leq 10MHz.
 - C. Inputs are measured separately one transition per measurement.
 - D. tPLZ and tPHZ are the same as tdis.
 - E. t_{PZL} and t_{PZH} are the same as t_{EN.}
 - F. tPLH and tPHL are the same as tPD.



Marking Information

(1) SOT353



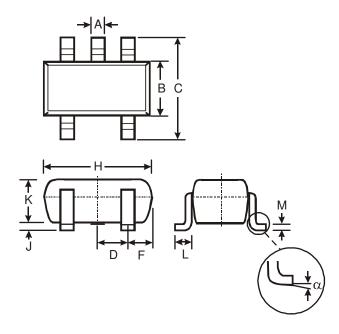
Part Number	Package	Identification Code	
74AUP1G125SE-7	SOT353	XY	

(2) X2-DFN0808-4, X1-DFN1010-6, X2-DFN1010-6, X2-DFN1409-6 and X2-DFN1410-6

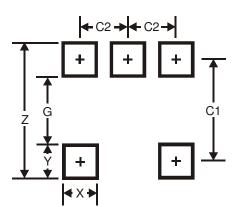
Part Number	Package	Identification Code
74AUP1G125FS3-7	X2-DFN0808-4	YY
74AUP1G125FW5-7	X1-DFN1010-6	QX
74AUP1G125FW4-7	X2-DFN1010-6	XY
74AUP1G125FX4-7	X2-DFN1409-6	HP
74AUP1G125FZ4-7	X2-DFN1410-6	XY



SOT353 Package Outline Dimensions and Suggested Pad Layout



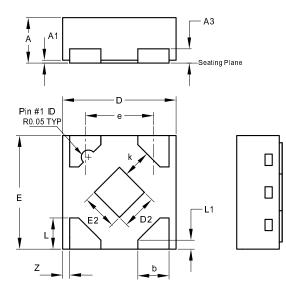
	SOT353					
Dim	Min	Max	Тур			
Α	0.10	0.30	0.25			
В	1.15	1.35	1.30			
С	2.00	2.20	2.10			
D		0.65 Typ	C			
F	0.40	0.45	0.425			
Н	1.80	2.20	2.15			
J	0	0.10	0.05			
К	0.90	1.00	1.00			
L	0.25	0.40	0.30			
Μ	0.10	0.22	0.11			
α	0°	8°	-			
A	II Dimer	nsions in	mm			



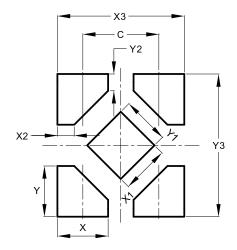
Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65



X2-DFN0808-4 Package Outline Dimensions and Suggested Pad Layout



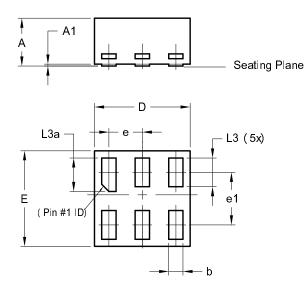
	X2-DFN0808-4					
Dim	Min	Max	Тур			
Α	0.25	0.35	0.30			
A1	0	0.04	0.02			
A3	-	-	0.13			
b	0.17	0.27	0.22			
D	0.75	0.85	0.80			
D2	0.15	0.35	0.25			
E	0.75	0.85	0.80			
E2	0.15	0.35	0.25			
е	-	-	0.48			
k	0.20	-	-			
L	0.17	0.27	0.22			
L1	0.02	0.12	0.07			
z	-	-	0.05			
A	II Dimens	sions in	mm			



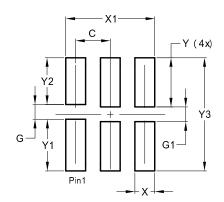
Dimensions	Value
С	0.480
X	0.320
X1	0.300
X2	0.106
X3	0.800
Y	0.320
Y1	0.300
Y2	0.106
Y3	0.900



X1-DFN1010-6 (Type B) Package Outline Dimensions and Suggested Pad Layout



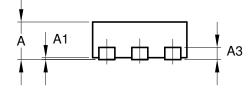
X1-DFN1010-6					
	(Ту	vpe B)			
Dim	Min	Max	Тур		
Α	-	0.50	0.39		
A1	-	0.04	-		
b	0.12	0.20	0.15		
D	0.95	1.050	1.00		
Е	0.95	1.050	1.00		
е		0.35 B	SC		
e1		0.55 B	SC		
L3	0.27	0.27 0.30 0.30			
L3a	0.32	0.40	0.35		
All	All Dimensions in mm				

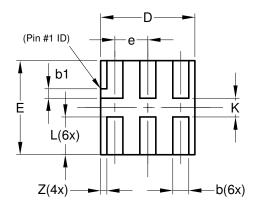


Dimensions	Value (in mm)
С	0.350
G	0.150
G1	0.150
Х	0.200
X1	0.900
Y	0.500
Y1	0.525
Y2	0.475
Y3	1.150

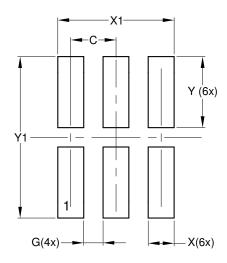


X2-DFN1010-6 Package Outline Dimensions and Suggested Pad Layout





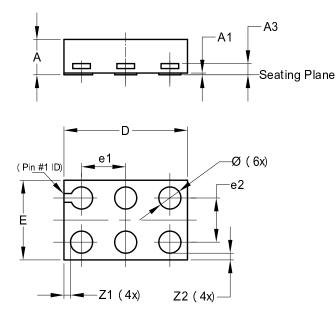
)	X2-DFN1010-6					
Dim	Min	Max	Тур			
Α		0.40	0.39			
A1	0.00	0.05	0.02			
A3			0.13			
b	0.14	0.20	0.17			
b1	0.05	0.15	0.10			
D	0.95	1.05	1.00			
Е	0.95	1.05	1.00			
е			0.35			
L	0.35	0.45	0.40			
К	0.15	_				
Z	_		0.065			
All D	imensi	ions in	mm			



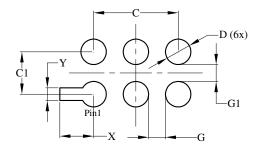
Dimensions	Value (in mm)
С	0.350
G	0.150
Х	0.200
X1	0.900
Y	0.550
Y1	1.250



X2-DFN1409-6 Package Outline Dimensions and Suggested Pad Layout



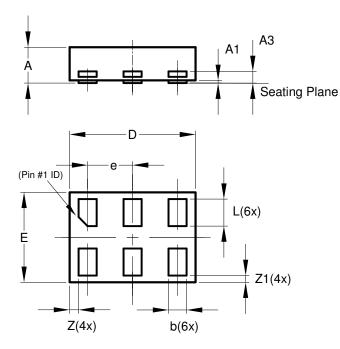
X2-DFN1409-6				
Dim	Min	Max	Тур	
Α	-	0.40	0.39	
A1	0	0.05	0.02	
A3	-	-	0.13	
Ø	0.20	0.30	0.25	
D	1.35	1.45	1.40	
ш	0.85	0.95	0.90	
e1	-	-	0.50	
e2	-	-	0.50	
Z1	-	-	0.075	
Z2	-	-	0.075	
All Dimensions in mm				



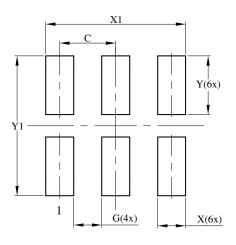
Dimensions	Value (in mm)
С	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
Х	0.400
Y	0.150



X2-DFN1410-6 Package Outline Dimensions and Suggested Pad Layout



X2-DFN1410-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
A3			0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
е			0.50	
L	0.25	0.35	0.30	
Z		_	0.10	
Z1	0.045	0.105	0.075	
All Dimensions in mm				



Dimensions	Value (in mm)	
С	0.500	
G	0.250	
Х	0.250	
X1	1.250	
Y	0.525	
Y1	1.250	



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